

Notice of References Cited		Application/Control No.	Applicant(s)/Patent Under Reexamination YAMAZAKI ET AL.	
		09/437,135	Examiner	Art Unit Erik Kielin 2813

U.S. PATENT DOCUMENTS

*	Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
A	US-5,000,113	03-1991	Wang et al.	118/723E
B	US-			
C	US-			
D	US-			
E	US-			
F	US-			
G	US-			
H	US-			
I	US-			
J	US-			
K	US-			
L	US-			
M	US-			

FOREIGN PATENT DOCUMENTS

*	Document Number Country Code-Number-Kind Code	Date MM-YYYY	Country	Name	Classification
N					
O					
P					
Q					
R					
S					
T					

NON-PATENT DOCUMENTS

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
U	Jiang et al. "Study of n-channel enhancement mode InP MISFETs" Chinese Journal of Semiconductors 9(5), September 1988, pp. 451-458.	
V	Sun et al. "High Quality MOSFET's with N ₂ O Annealed Thin TEOS Gate Oxide" IEEE 1993 International Symposium on VLSI Technology, May 1993, pp. 109-111.	
W		
X		

*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.